# INTEGRATED CIRCUITS



Product specification IC23 Data Handbook 1997 Feb 03



Philips Semiconductors

## 74ABT534A

#### **FEATURES**

- 8-bit positive edge triggered register
- 3-State output buffers
- Output capability: +64mA/-32mA
- Latch-up protection exceeds 500mA per Jedec JC40.2 Std 17
- ESD protection exceeds 2000 V per MIL STD 883 Method 3015 and 200 V per Machine Model
- Power-up 3-State

#### DESCRIPTION

The 74ABT534A high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 74ABT534A is an 8-bit, edge triggered register coupled to eight 3-State output buffers. The two sections of the device are controlled independently by the clock (CP) and Output Enable ( $\overline{OE}$ ) control gates.

The register is fully edge triggered. The state of each D input, one set-up time before the Low-to-High clock transition, is transferred to the corresponding flip-flop's output.

The 3-State output buffers are designed to drive heavily loaded 3-State buses, MOS memories, or MOS microprocessors. The active-Low Output Enable ( $\overline{\text{OE}}$ ) controls all eight 3-State buffers independent of the clock operation.

When  $\overline{OE}$  is Low, the stored data appears at the outputs. When  $\overline{OE}$  is High, the outputs are in the High-impedance "OFF" state, which means they will neither drive nor load the bus.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	PARAMETER CONDITIONS T <sub>amb</sub> = 25°C; GND = 0V			
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay CP to Qn	$C_{L} = 50 pF; V_{CC} = 5V$	3.3 3.6	ns	
C <sub>IN</sub>	Input capacitance	$V_I = 0V \text{ or } V_{CC}$	3.5	pF	
C <sub>OUT</sub>	Output capacitance	Outputs disabled; $V_O = 0V$ or $V_{CC}$	6.5	pF	
I <sub>CCZ</sub>	Total supply current	Outputs disabled; $V_{CC}$ =5.5V	100	μΑ	

### **ORDERING INFORMATION**

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
20-Pin Plastic DIP	–40°C to +85°C	74ABT534A N	74ABT534A N	SOT146-1
20-Pin plastic SO	–40°C to +85°C	74ABT534A D	74ABT534A D	SOT163-1
20-Pin Plastic SSOP Type II	–40°C to +85°C	74ABT534A DB	74ABT534A DB	SOT339-1
20-Pin Plastic TSSOP Type I	–40°C to +85°C	74ABT534A PW	74ABT534APW DH	SOT360-1

### **PIN CONFIGURATION**

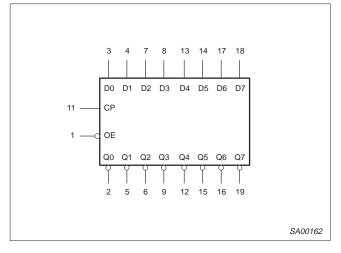
		o ∨cc
Q0 2	1	9 <del>Q</del> 7
D0 3	1	8 D7
D1 4	1	7 D6
Q1 5	1	6 <del>Q</del> 6
Q2 6	1	5 Q5
D2 7	1	4 D5
D3 8	1	3 D4
Q3 9	1	2 <del>Q</del> 4
GND 10	1	1 CP
l		0100101
		SA00161

### PIN DESCRIPTION

PIN NUMBER	SYMBOL	FUNCTION
1	ŌĒ	Output enable input (active-Low)
3, 4, 7, 8, 13, 14, 17, 18	D0-D7	Data inputs
2, 5, 6, 9, 12, 15, 16, 19	<u>Q</u> 0-Q7	Inverting 3-State outputs
11	СР	Clock pulse input (active rising edge)
10	GND	Ground (0V)
20	V <sub>CC</sub>	Positive supply voltage

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### LOGIC SYMBOL

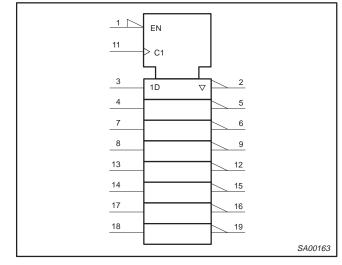


### **FUNCTION TABLE**

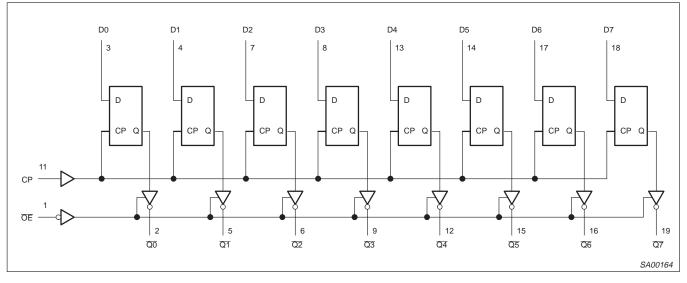
	INPUTS		INTERNAL	OUTPUTS	OPERATING MODE
ŌĒ	СР	Dn	REGISTER	$\overline{Q}0 - \overline{Q}7$	
L L	$\stackrel{\land}{\leftarrow}$	l h	L H	H L	Latch and read register
L	\$	Х	NC	NC	Hold
ΤT	$\stackrel{}{\uparrow}$	X Dn	NC Dn	Z Z	Disable outputs

### LOGIC DIAGRAM

### LOGIC SYMBOL (IEEE/IEC)



- H = High voltage level
- High voltage level one set-up time prior to the Low-to-High clock transition h =
- L Low voltage level =
- Low voltage level one set-up time prior to the Low-to-High clock transition L =
- No change Don't care NC=
- X = Z = ↑ = ↓ =
- High impedance "off" state
- Low-to-High clock transition not a Low-to-High clock transition



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### ABSOLUTE MAXIMUM RATINGS<sup>1, 2</sup>

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V <sub>CC</sub>	DC supply voltage		-0.5 to +7.0	V
I <sub>IK</sub>	DC input diode current	V <sub>1</sub> < 0	-18	mA
VI	DC input voltage <sup>3</sup>		-1.2 to +7.0	V
I <sub>OK</sub>	DC output diode current	V <sub>O</sub> < 0	-50	mA
V <sub>OUT</sub>	DC output voltage <sup>3</sup>	output in Off or High state	-0.5 to +5.5	V
I <sub>OUT</sub>	DC output current	output in Low state	128	mA
T <sub>stg</sub>	Storage temperature range		-65 to 150	°C

NOTES:

1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.

3. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

### **RECOMMENDED OPERATING CONDITIONS**

SYMBOL	PARAMETER	LIM		
STMBOL	FARAIVETER	Min	Max	UNIT
V <sub>CC</sub>	DC supply voltage	4.5	5.5	V
VI	Input voltage	0	V <sub>CC</sub>	V
V <sub>IH</sub>	High-level input voltage	2.0		V
V <sub>IL</sub>	Low-level Input voltage		0.8	V
I <sub>ОН</sub>	High-level output current		-32	mA
I <sub>OL</sub>	Low-level output current		64	mA
Δt/Δv	Input transition rise or fall rate	0	5	ns/V
T <sub>amb</sub>	Operating free-air temperature range	-40	+85	°C

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### **DC ELECTRICAL CHARACTERISTICS**

			LIMITS						
SYMBOL	PARAMETER	TEST CONDITIONS	Ta	<sub>mb</sub> = +25	°C	T <sub>amb</sub> = to +	⊨–40°C 85°C	UNIT	
			Min	Тур	Max	Min	Max	1	
V <sub>IK</sub>	Input clamp voltage	$V_{CC} = 4.5V; I_{IK} = -18mA$		-0.9	-1.2		-1.2	V	
		$V_{CC}$ = 4.5V; $I_{OH}$ = -3mA; $V_I$ = $V_{IL}$ or $V_{IH}$	2.5	2.9		2.5		V	
V <sub>OH</sub>	High-level output voltage	$V_{CC}$ = 5.0V; $I_{OH}$ = -3mA; $V_I$ = $V_{IL}$ or $V_{IH}$	3.0	3.4		3.0		V	
		$V_{CC}$ = 4.5V; $I_{OH}$ = -32mA; $V_I$ = $V_{IL}$ or $V_{IH}$	2.0	2.4		2.0		V	
V <sub>OL</sub>	Low-level output voltage	$V_{CC}$ = 4.5V; $I_{OL}$ = 64mA; $V_I$ = $V_{IL}$ or $V_{IH}$		0.42	0.55		0.55	V	
I <sub>I</sub>	Input leakage current	V <sub>CC</sub> = 5.5V; V <sub>I</sub> = GND or 5.5V		±0.01	±1.0		±1.0	μΑ	
I <sub>OFF</sub>	Power-off leakage current	$V_{CC}$ = 0.0V; V <sub>I</sub> or V <sub>O</sub> $\leq$ 4.5V		±5.0	±100		±100	μΑ	
I <sub>PU</sub> /I <sub>PD</sub>	Power-up/down 3-State output current <sup>3</sup>	$V_{\underline{CC}} = 2.0V; V_{O} = 0.5V; V_{I} = GND \text{ or } V_{\underline{CC}};$ $V_{OE} = V_{\underline{CC}}$		±5.0	±50		±50	μA	
I <sub>OZH</sub>	3-State output High current	$V_{CC}$ = 5.5V; $V_O$ = 2.7V; $V_I$ = $V_{IL}$ or $V_{IH}$		0.1	10		10	μΑ	
I <sub>OZL</sub>	3-State output Low current	$V_{CC}$ = 5.5V; $V_{O}$ = 0.5V; $V_{I}$ = $V_{IL}$ or $V_{IH}$		-0.1	-10		-10	μΑ	
I <sub>CEX</sub>	Output High leakage current	$V_{CC}$ = 5.5V; $V_{O}$ = 5.5V; $V_{I}$ = GND or $V_{CC}$		0.1	50		50	μΑ	
Ι <sub>Ο</sub>	Output current <sup>1</sup>	$V_{CC} = 5.5V; V_{O} = 2.5V$	-50	-100	-180	-50	-180	mA	
I <sub>CCH</sub>		$V_{CC}$ = 5.5V; Outputs High, $V_I$ = GND or $V_{CC}$		100	250		250	μΑ	
I <sub>CCL</sub>	Quiescent supply current	$V_{CC}$ = 5.5V; Outputs Low, $V_{I}$ = GND or $V_{CC}$		24	30		30	mA	
I <sub>CCZ</sub>	]	$V_{CC}$ = 5.5V; Outputs 3-State; V <sub>I</sub> = GND or V <sub>CC</sub>		100	250		250	μΑ	
$\Delta I_{CC}$	Additional supply current per input pin <sup>2</sup>	$V_{CC}$ = 5.5V; one input at 3.4V, other inputs at $V_{CC}$ or GND		0.5	1.5		1.5	mA	

#### NOTES:

1. Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

2. This is the increase in supply current for each input at 3.4V. 3 This parameter is valid for any V<sub>CC</sub> between 0V and 2.1V with a transition time of up to 10msec. For V<sub>CC</sub> = 2.1V to V<sub>CC</sub> = 5V  $\pm$  10%, a transition time of up to 100µsec is permitted.

### **AC CHARACTERISTICS**

GND = 0V,  $t_R = t_F$  = 2.5ns,  $C_L$  = 50pF,  $R_L$  = 500 $\Omega$ 

					LIMITS			
SYMBOL	PARAMETER WAVEFORM		ŗ	<sub>amb</sub> = +25° V <sub>CC</sub> = +5.0V	C /	T <sub>amb</sub> = +8 V <sub>CC</sub> = +5	UNIT	
				Тур	Max	Min	Max	
f <sub>MAX</sub>	Maximum clock frequency	1	125	350		125		ns
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay CP to Qn	1	2.0 <sup>1</sup> 2.4 <sup>1</sup>	3.3 3.6	4.2 <sup>1</sup> 4.7 <sup>1</sup>	2.0 2.4	5.0 <sup>1</sup> 5.1 <sup>1</sup>	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output enable time to High and Low level	3 4	1.0 2.6	3.1 3.9	4.2 4.9 <sup>1</sup>	1.0 2.6	5.0 5.5 <sup>1</sup>	ns
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output disable time from High and Low level	3 4	1.8 <sup>1</sup> 1.6 <sup>1</sup>	3.3 2.8	4.3 <sup>1</sup> 3.6 <sup>1</sup>	1.8 <sup>1</sup> 1.6 <sup>1</sup>	4.6 <sup>1</sup> 4.1 <sup>1</sup>	ns

NOTE:

1. This datasheet limit may vary among suppliers.

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### AC SETUP REQUIREMENTS

GND = 0V,  $t_R = t_F = 2.5 \text{ns}$ ,  $C_L = 50 \text{pF}$ ,  $R_L = 500 \Omega$ 

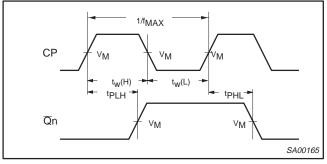
				LIMI	rs	
SYMBOL	PARAMETER	WAVEFORM	T <sub>amb</sub> = V <sub>CC</sub> =	: +25°C : +5.0V	T <sub>amb</sub> = -40 to +85°C V <sub>CC</sub> = +5.0V ±0.5V	UNIT
			Min	Тур	Min	
t <sub>s</sub> (H) t <sub>s</sub> (L)	Setup time, High or Low Dn to CP	2	1.0 <sup>1</sup> 1.0 <sup>1</sup>	0.4 0.3	1.0 <sup>1</sup> 1.0 <sup>1</sup>	ns
t <sub>h</sub> (H) t <sub>h</sub> (L)	Hold time, High or Low Dn to CP	2	0.5 0.5	-0.3 -0.4	0.5 0.5	ns
t <sub>w</sub> (H) t <sub>w</sub> (L)	CP pulse width High or Low	1	1.5 <sup>1</sup> 2.0 <sup>1</sup>	0.8 1.0	1.5 <sup>1</sup> 2.0 <sup>1</sup>	ns

NOTE:

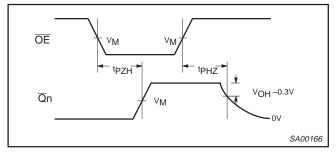
1. This datasheet limit may vary among suppliers.

### AC WAVEFORMS

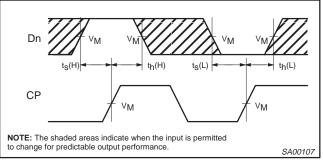
 $V_{M}$  = 1.5V,  $V_{IN}$  = GND to 3.0V



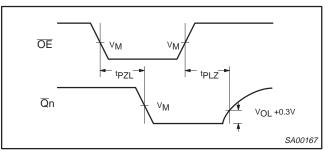
Waveform 1. Propagation Delay, Clock Input to Output, Clock Pulse Width, and Maximum Clock Frequency



Waveform 3. 3-State Output Enable Time to High Level and Output Disable Time from High Level



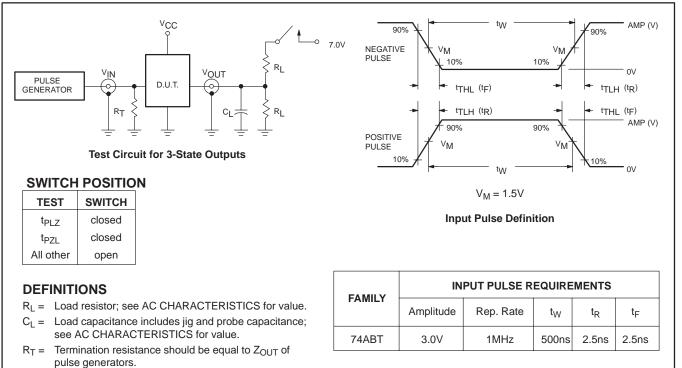
Waveform 2. Data Setup and Hold Times



Waveform 4. 3-State Output Enable Time to Low Level and Output Disable Time from Low Level

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### **TEST CIRCUIT AND WAVEFORM**



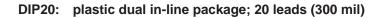
SA00012

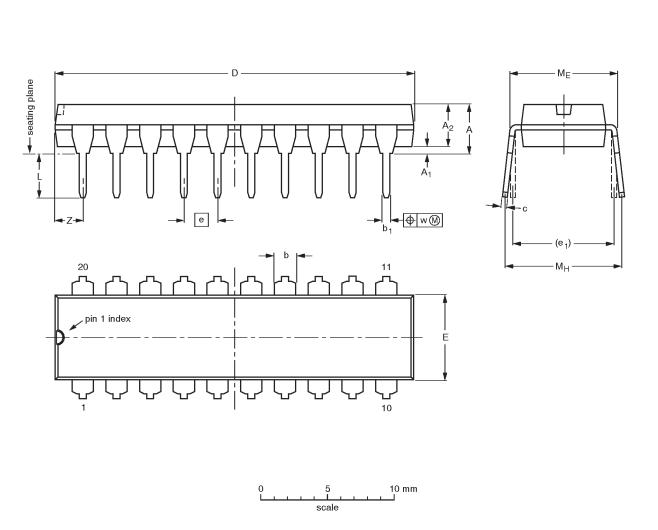
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### Product specification

SOT146-1

# 74ABT534A





#### DIMENSIONS (inch dimensions are derived from the original mm dimensions)

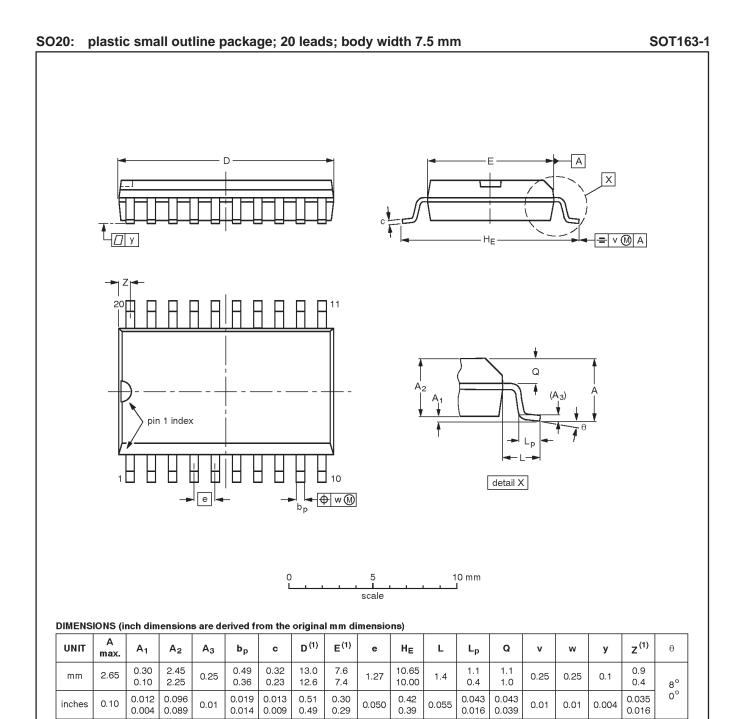
UNIT	A max.	A <sub>1</sub> min.	A <sub>2</sub> max.	b	b <sub>1</sub>	с	D <sup>(1)</sup>	Е <sup>(1)</sup>	e	e <sub>1</sub>	L	M <sub>E</sub>	M <sub>H</sub>	w	Z <sup>(1)</sup> max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	0.36 0.23	26.92 26.54	6.40 6.22	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.0
inches	0.17	0.020	0.13	0.068 0.051	0.021 0.015	0.014 0.009	1.060 1.045	0.25 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.078

#### Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE	
VERSION	IEC	IEC JEDEC		EIAJ		ISSUE DATE	
SOT146-1			SC603			<del>-92-11-17</del> 95-05-24	

## 74ABT534A

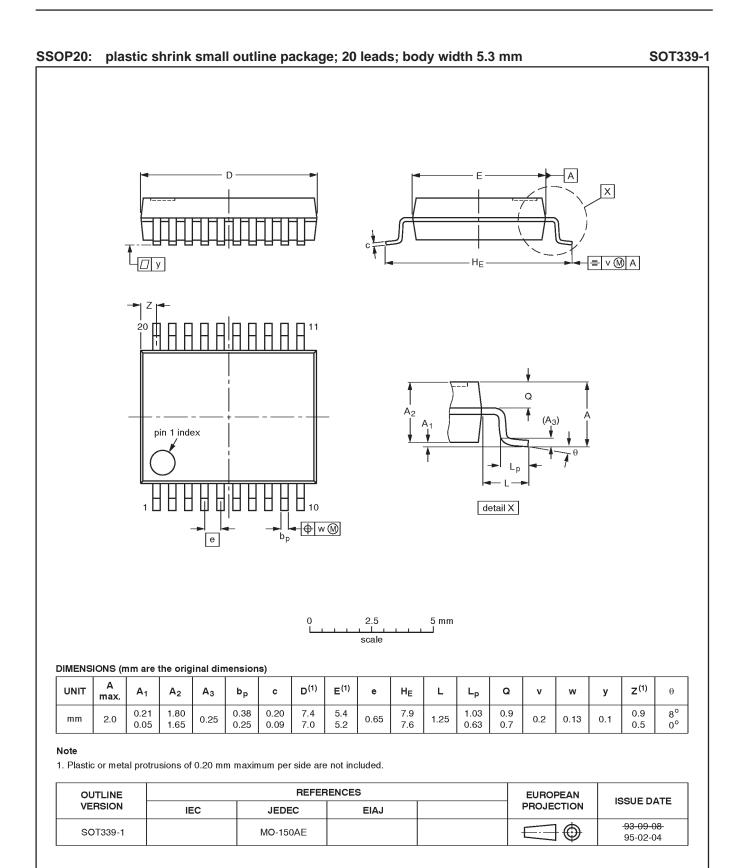


#### Note

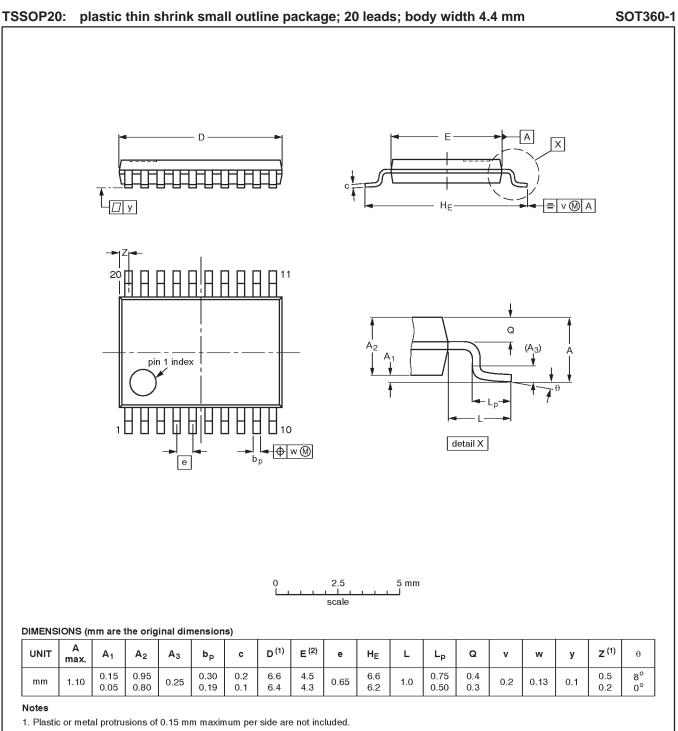
1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT163-1	075E04	MS-013AC				<del>-92-11-17</del> 95-01-24

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2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN	ISSUE DATE	
	IEC	JEDEC	EIAJ		PROJECTION	1550E DATE	
	SOT360-1		MO-153AC				<del>-93-06-16</del> 95-02-04

## 74ABT534A

DEFINITIONS				
Data Sheet Identification	Product Status	Definition		
Objective Specification	Formative or in Design	This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice.		
Preliminary Specification	Preproduction Product	This data sheet contains preliminary data, and supplementary data will be published at a later date. Phili Semiconductors reserves the right to make changes at any time without notice in order to improve desi and supply the best possible product.		
Product Specification Full Production		This data sheet contains Final Specifications. Philips Semiconductors reserves the right to make changes at any time without notice, in order to improve design and supply the best possible product.		

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